

■ Features

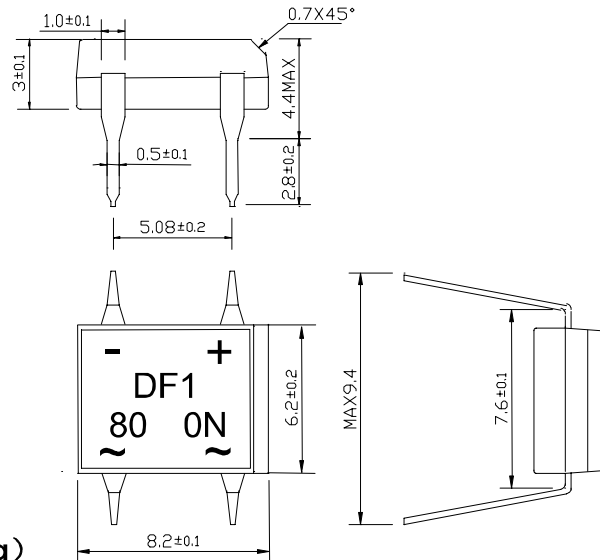
- $I_o$  1.0A
- $V_{RRM}$  200V~1000V
- Glass passivated chip
- High surge forward current capability
- Supersmall size

■ Applications

- General purpose 1 phase Bridge rectifier applications

Outline Dimensions and Mark

Unit: mm



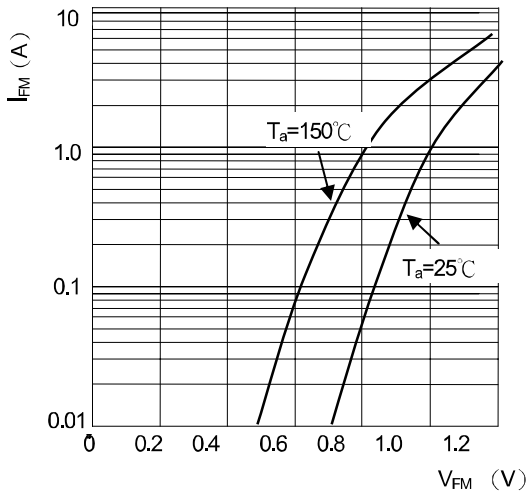
■ Limiting Values (Absolute Maximum Rating)

| Item                                 | Symbol    | Unit             | Conditions   | DF1        |     |     |     |      |
|--------------------------------------|-----------|------------------|--|------------|-----|-----|-----|------|
|                                      |           |                  |  | 20         | 40  | 60  | 80  | 100  |
| Storage Temperature                  | $T_{stg}$ | °C               |  | -40 ~ +150 |     |     |     |      |
| Junction Temperature                 | $T_j$     | °C               |  | +150       |     |     |     |      |
| Repetitive Peak Reverse Voltage      | $V_{RRM}$ | V                |  | 200        | 400 | 600 | 800 | 1000 |
| Average Rectified Output Current     | $I_o$     | A                | 50Hz sine wave, R-load, $T_a=25^\circ\text{C}$                                     | 1          |     |     |     |      |
| Surge(Non-repetitive)Forward Current | $I_{FSM}$ | A                | 50Hz sine wave, 1 cycle, $T_a=25^\circ\text{C}$                                    | 30         |     |     |     |      |
| Current Squared Time                 | $I^2t$    | A <sup>2</sup> s | $1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$ ,<br>Rating of per diode | 4.5        |     |     |     |      |

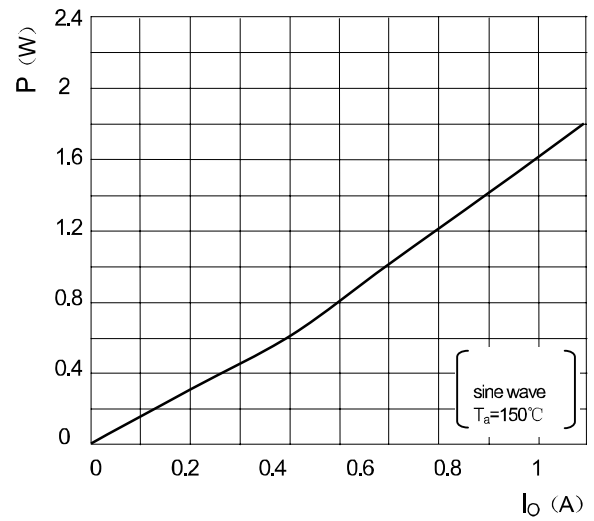
■ Electrical Characteristics ( $T_a=25^\circ\text{C}$  Unless otherwise specified)

| Item                 | Symbol           | Unit          | Test Condition  | Max  |
|----------------------|------------------|---------------|---|------|
| Peak Forward Voltage | $V_{FM}$         | V             | $I_{FM}=0.5\text{A}$ , Pulse measurement, Rating of per diode | 1.05 |
| Peak Reverse Current | $I_{RRM1}$       | $\mu\text{A}$ | $V_{RM}=V_{RRM}$ , Pulse measurement, Rating of per diode     | 10   |
| Thermal Resistance   | $R_{\theta J-A}$ | °C/W          | Between junction and ambient ,On alumina substrate            | 68   |
|                      | $R_{\theta J-L}$ |               | Between junction and lead                                     | 15   |

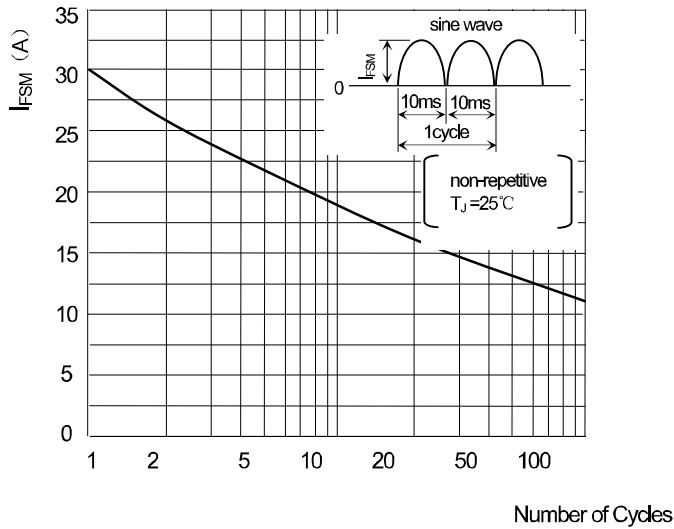
■ Characteristics(Typical)



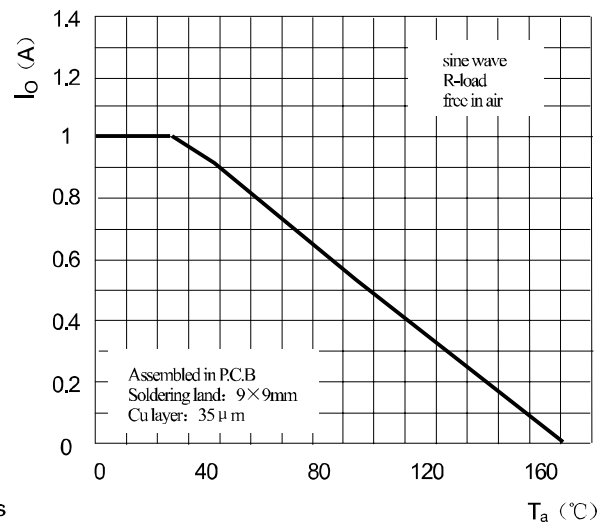
Forward Characteristics



P- $I_o$  Curve



Surge Forward Current Capability



$I_o$ - $T_a$  Curve